

MPSA29



NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 500 mA. Sourced from Process 03. See MPSA28 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CES}	Collector-Emitter Voltage	100	V	
V _{CBO}	Collector-Base Voltage	100	V	
V_{EBO}	Emitter-Base Voltage	12	V	
Ic	Collector Current - Continuous	800	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

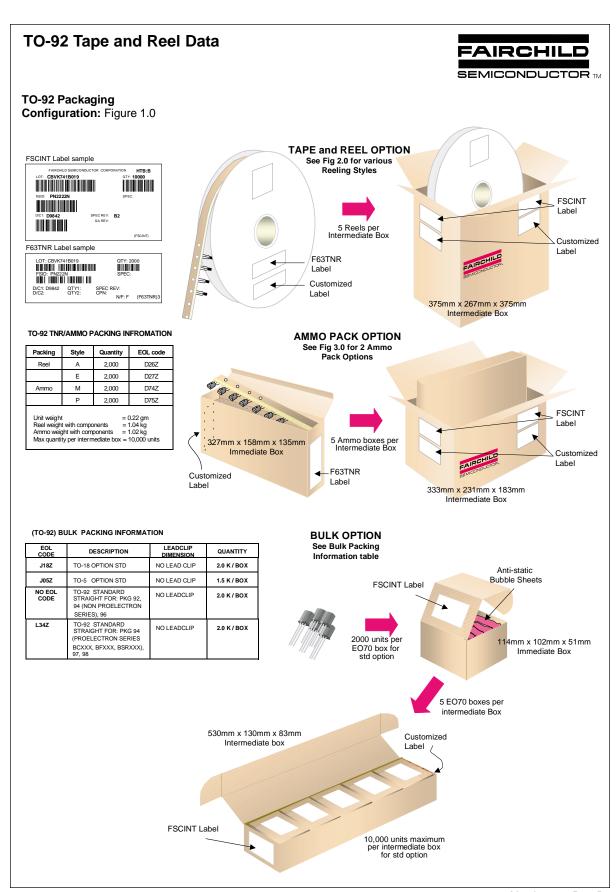
Symbol	Characteristic	Max	Units
		MPSA29	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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NPN Darlington Transistor (continued)

Electr	Electrical Characteristics TA = 25°C unless otherwise noted					
Symbol	Parameter	Test Conditions	Min	Max	Units	
OFF CHA	RACTERISTICS					
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage*	$I_C = 100 \mu\text{A}, I_B = 0$	100		V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	100		V	
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	12		V	
I _{CBO}	Collector Cutoff Current	$V_{CB} = 80 \text{ V}, I_{E} = 0$		100	nA	
I _{CES}	Collector Cutoff Current	$V_{CE} = 80 \text{ V}, I_{E} = 0$		500	nA	
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		100	nA	
ON CHAR	RACTERISTICS* DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \text{ mA}$	10,000			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.01 \text{ mA}$ $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$	10,000	1.2 1.5	V	
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$		2.0	V	
	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 100 \text{ MHz}$	125		MHz	
C _{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		8.0	pF	
	II.	1				

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

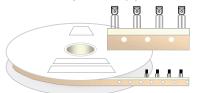


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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



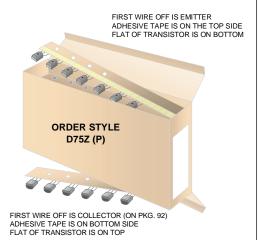
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

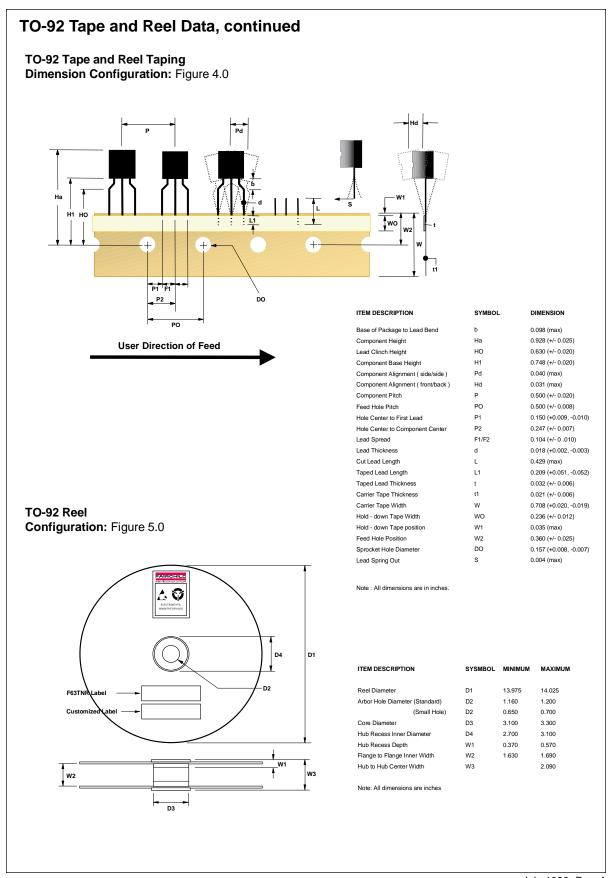
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





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TO-92 Package Dimensions FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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0.095 0.084 2.13

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